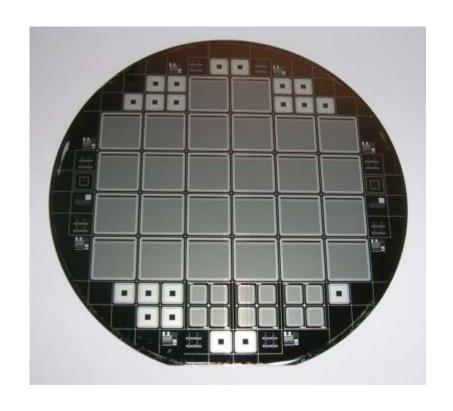
MICRON mini and PAD detectors 140 and 300 μ m thick

300	Tthick	Res	Spray	Minis	Pads		Tthick	Res	Spray	Minis	Pads
μm	[µm]	$[k\Omega]$	dose	#	#	140 µm	[µm]	$[k\Omega]$	dose	#	#
2328-3	300	30	High			2437-5	140	30	High	9	9
2328-4	300	30	High	9	9	2437-6	140	30	High		
2328-5	300	30	Medium			2437-3	140	30	Medium		
2328-6	300	30	Medium	9	9	2437-4	140	30	Medium	9	9
2328-7	300	30	Low	9	9	2437-2	140	30	Low	9	9
2328-8	300	30	No spray	9	9	2437-1	140	30	No spray	9	9
						2438-1	140	10	High		
						2438-2	140	10	High	9	9
						2438-3	140	10	Medium	9	9
						2438-4	140	10	Medium		
						2438-6	140	10	No spray		9

CNM mini and PAD detectors

26 mini's (M)/wafer20 pads (P)/wafer



7th RD50 Workshop

Reminder of RD50 process

Technology	Wafers	Growing method	Туре	Wafer origin	Comments
D in N	4	MCZ	N	RD50	>500 Ω·cm, 300 μm
P-in-N	2	EPI	N	RD50	thickness ~ 150 µm
	4	MCZ	Р	RD50	>2 kΩ⋅cm, 300 μm
N-in-P	4	FZ	Р	CNM	
N-IN-P	4	FZ	Р	CNM	Oxygen enriched DOFZ
	2	EPI	Р	RD50	thickness ~ 150 µm
N-in-N	2	FZ	N	CNM	Single side processing
TOTAL	22				

104 M, 80 P 52 M, 40 P 104 M, 80 P 104 M, 80 P 104 M, 80 P 52 M, 40 P 52 M, 40 P

572 M, 440 P, 5 flavours



Possible irradiation scenario (CERN-PS) 6 fluences?

1 pre-inversion, 3E14, 6E14, 1E15, 1E16, 2E16 cm⁻².

If 2 detectors are required for redundancy, every set would be composed by 12 devices. In some cases only four complete sets would be available for irradiation, despite the high number of devices produced!